

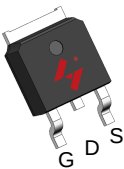
HY3403D/U/V

N-Channel Enhancement Mode MOSFET

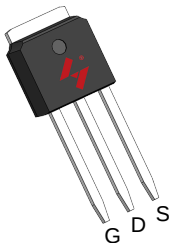
Feature

- 30V/100A
 $R_{DS(ON)} = 2.4m\Omega (typ.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 2.9m\Omega (typ.) @ V_{GS} = 4.5V$
- 100% Avalanche Tested
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

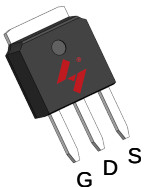
Pin Description



TO-252-2L



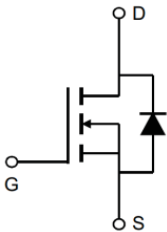
TO-251-3L



TO-251-3S

Applications

- Systems High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use



N-Channel MOSFET

Ordering and Marking Information

 D HY3403 YYXXXJWW G	 U HY3403 YYXXXJWW G	 V HY3403 YYXXXJWW G	Package Code D: TO-252-2L U: TO-251-3L V: TO-251-3S Date Code YYXXX WW Assembly Material G: Halogen Free
---	---	---	---

Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plateTermination finish; which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-Free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines “Green” to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	100	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	400	A
I _D	Continuous Drain Current	Tc=25°C	100	A
		Tc=100°C	70	A
P _D	Maximum Power Dissipation	Tc=25°C	60	W
		Tc=100°C	30	W
R _{θJC}	Thermal Resistance, Junction-to-Case		2.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		110	°C/W
E _{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH	184	mJ

Note: * Repetitive rating; pulse width limited by max. junction temperature.
 ** Surface mounted on FR-4 board.
 *** Limited by T_{Jmax}, starting T_J=25°C, L = 0.3mH, R_G = 25Ω, V_{GS} = 10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3403			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
		T _J =125°C	-	-	50	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.5	3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)*}	Drain-Source On-State Resistance	V _{GS} =10V, I _{DS} =50A	-	2.4	3.0	mΩ
		V _{GS} =4.5V, I _{DS} =50A	-	2.9	3.6	
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =50A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =50A, dI _{SD} /dt=100A/μs	-	23	-	ns
Q _{rr}	Reverse Recovery Charge		-	58	-	nC

Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3403			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =24V, Frequency=1.0MHz	-	4726	-	pF
C _{oss}	Output Capacitance		-	469	-	
C _{rss}	Reverse Transfer Capacitance		-	322	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V,R _G =4Ω, I _{DS} =50A,V _{GS} =10V	-	13	-	ns
T _r	Turn-on Rise Time		-	11	-	
t _{d(OFF)}	Turn-off Delay Time		-	41	-	
T _f	Turn-off Fall Time		-	14	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =24V, V _{GS} =10V, I _D =50A	-	120	-	nC
Q _{gs}	Gate-Source Charge		-	9	-	
Q _{gd}	Gate-Drain Charge		-	26	-	

Note: *Pulse test, pulse width ≤ 300us, duty cycle ≤ 2%

Typical Operating Characteristics

Figure 1: Power Dissipation

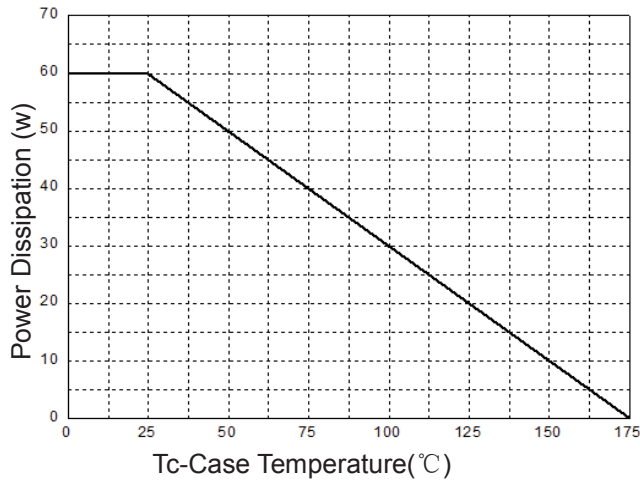


Figure 2: Drain Current

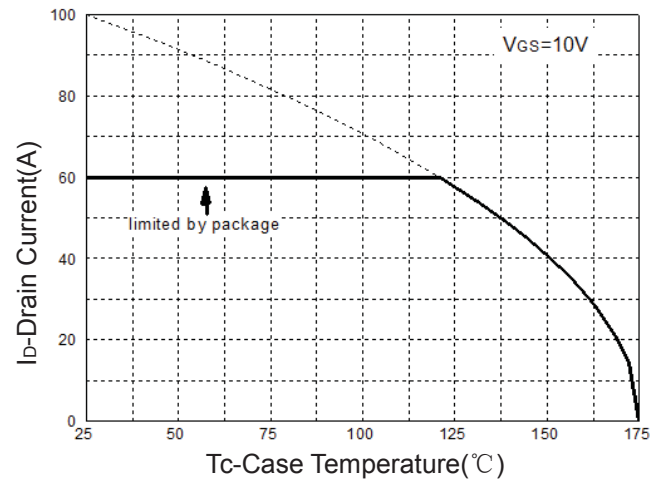


Figure 3: Safe Operation Area

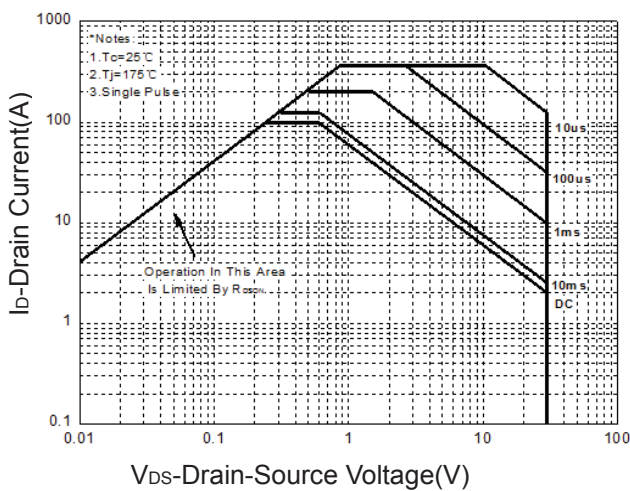


Figure 4: Thermal Transient Impedance

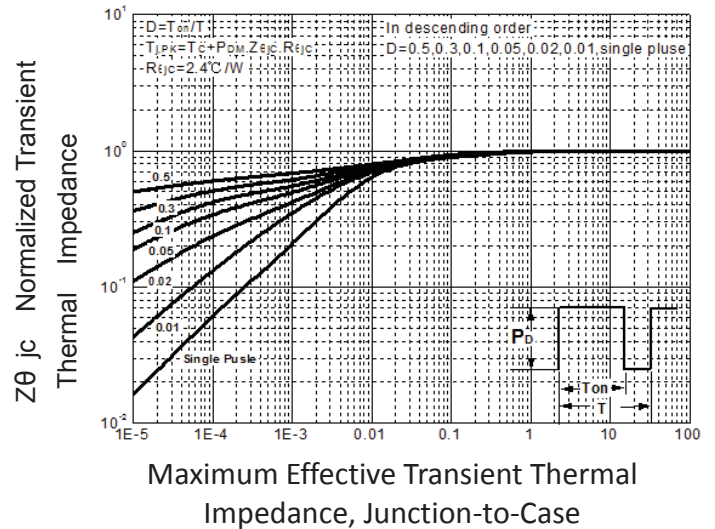


Figure 5: Output Characteristics

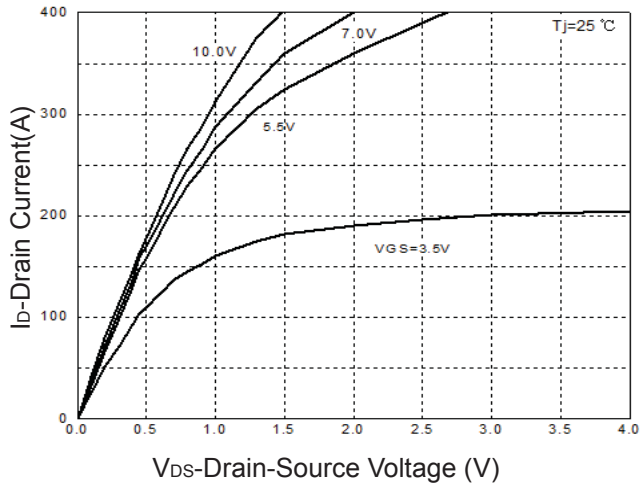
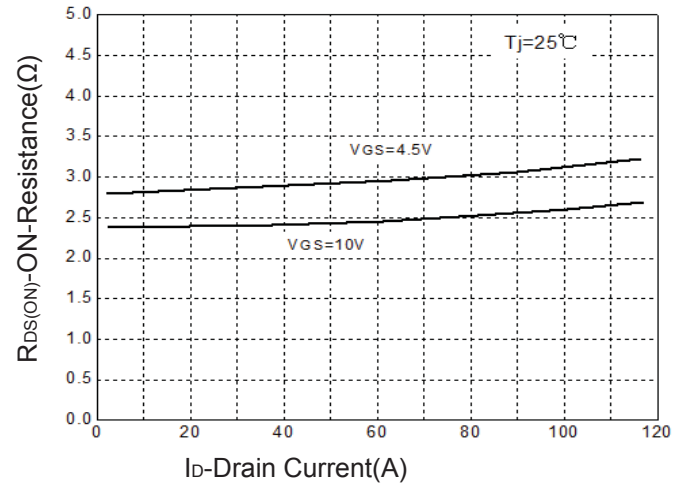


Figure 6: Drain-Source On Resistance



Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

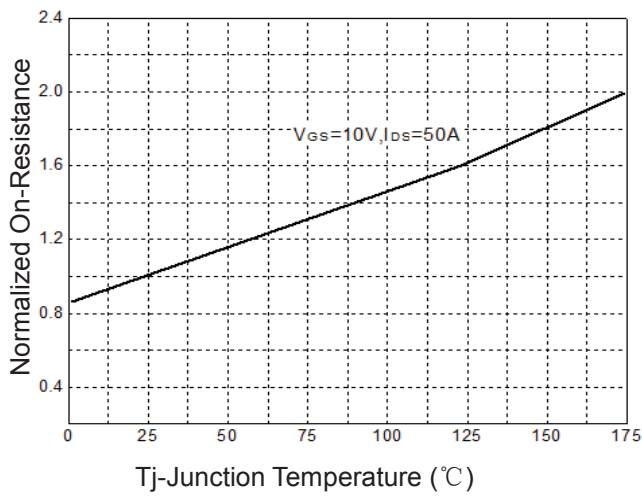


Figure 8: Source-Drain Diode Forward

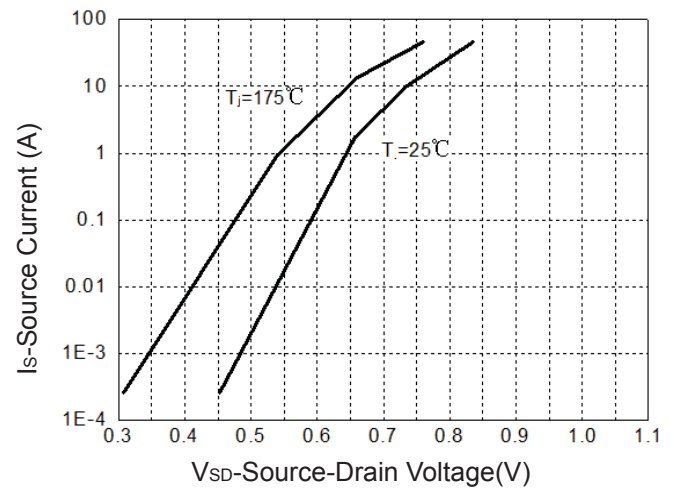


Figure 9: Capacitance Characteristics

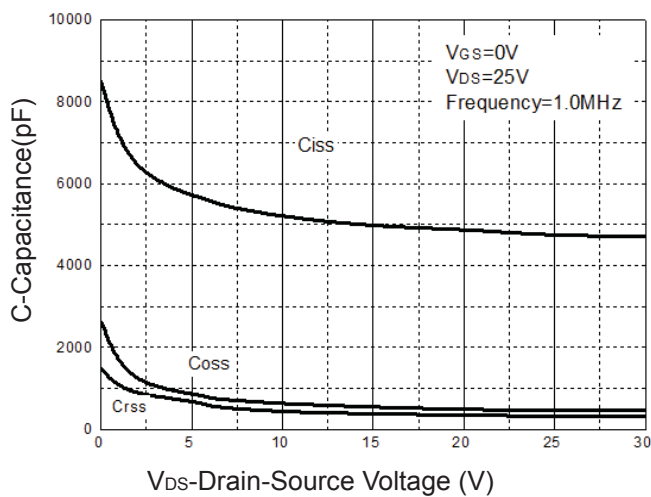
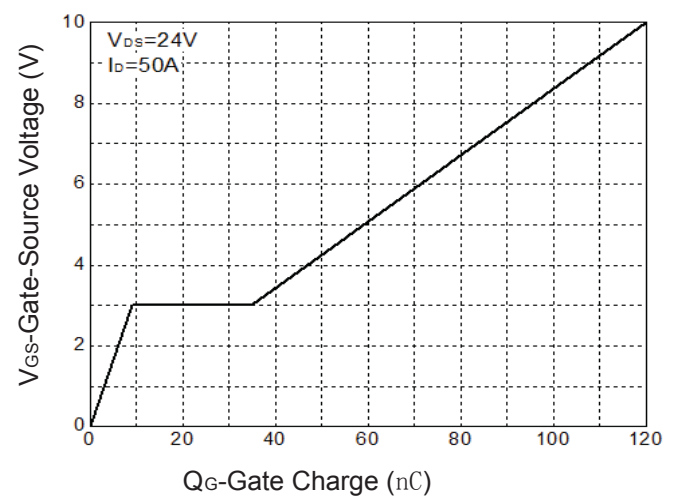
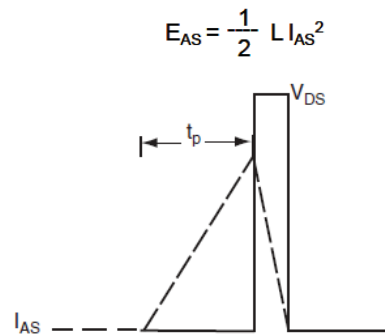
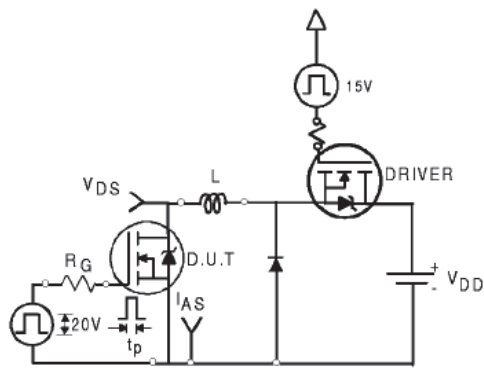


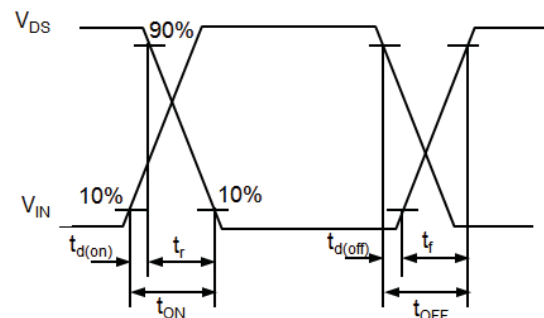
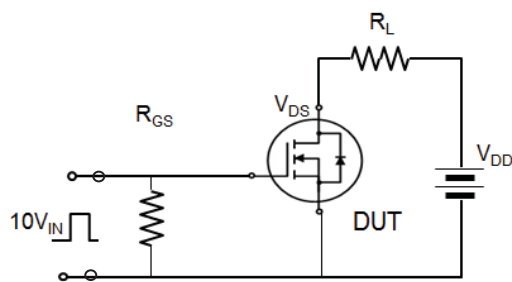
Figure 10: Gate Charge Characteristics



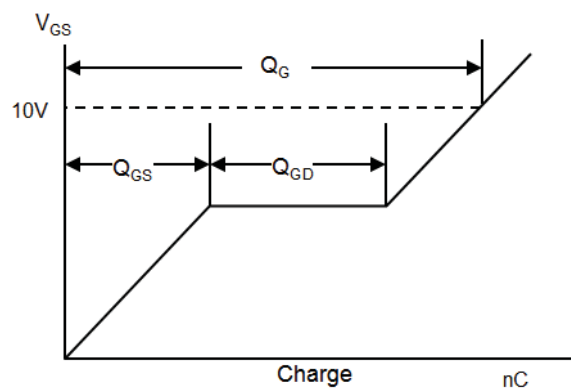
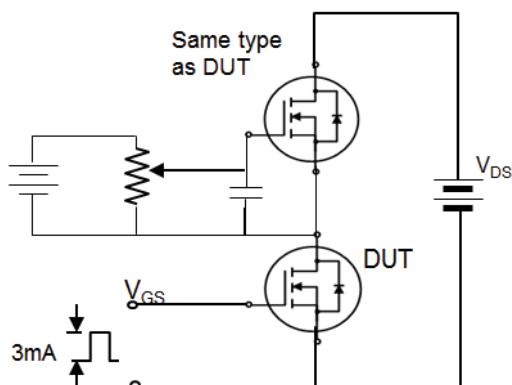
Avalanche Test Circuit



Switching Time Test Circuit and Waveforms



Gate Charge Test Circuit and Waveforms



Device Per Unit

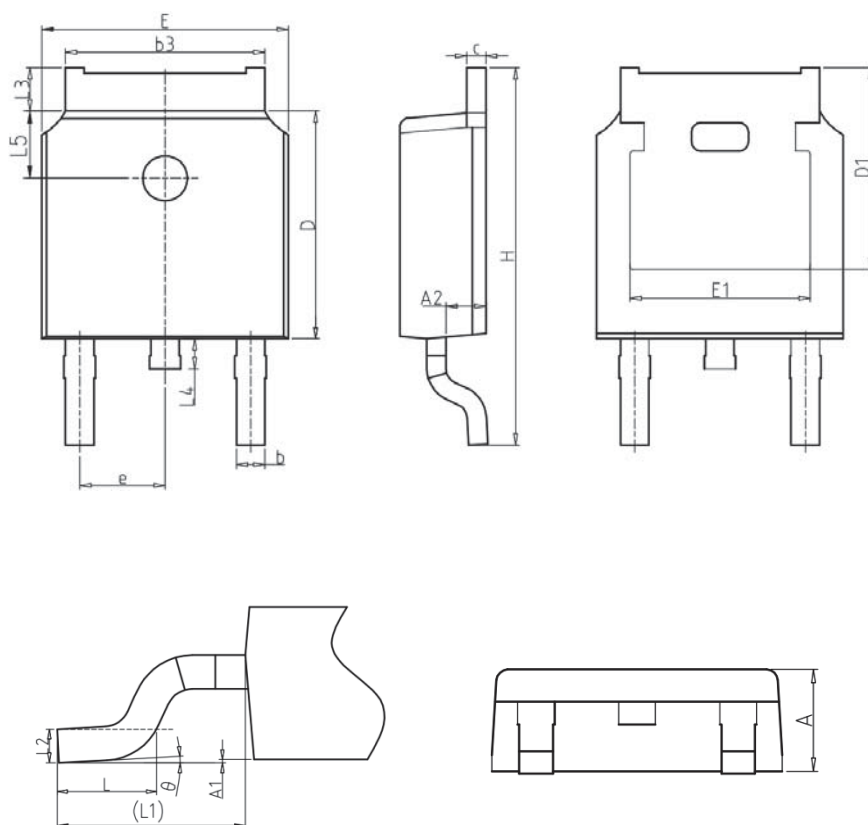
Package Type	Unit	Quantity
TO-252-2L	Tube	75
TO-252-2L	Reel	2500
TO-251-3L	Tube	75
TO-251-3S	Tube	75

Package Information

TO-252-2L

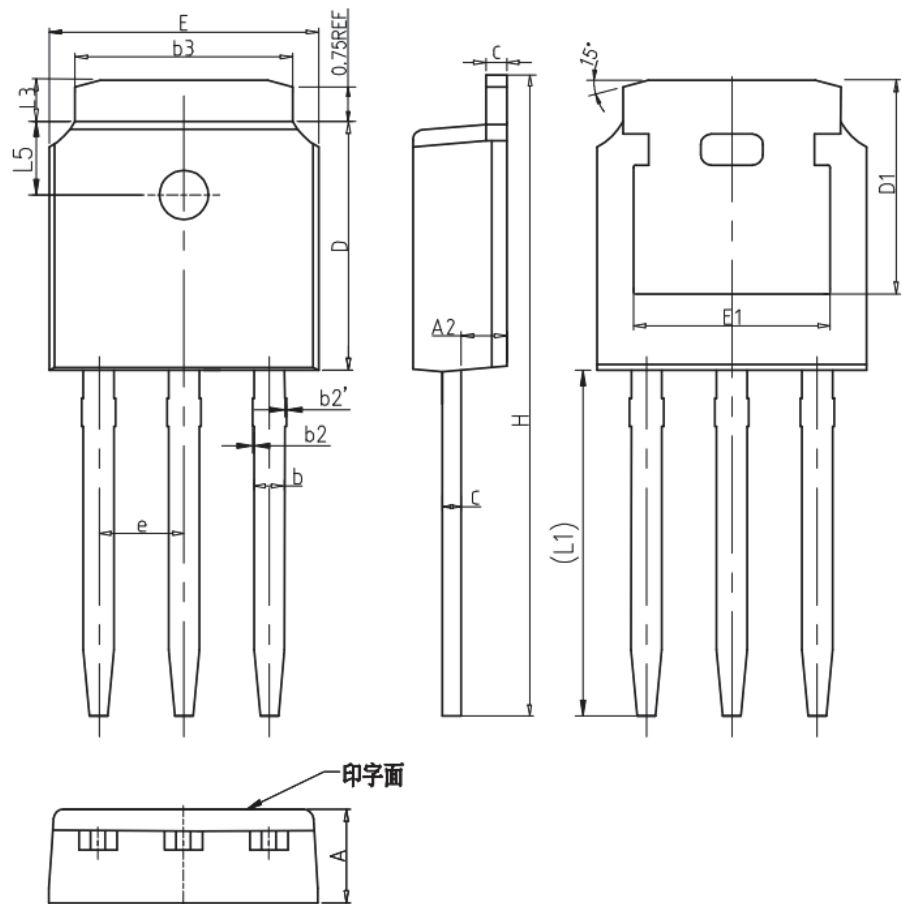
COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	-	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°



HY3403D/U/V

TO-251-3L

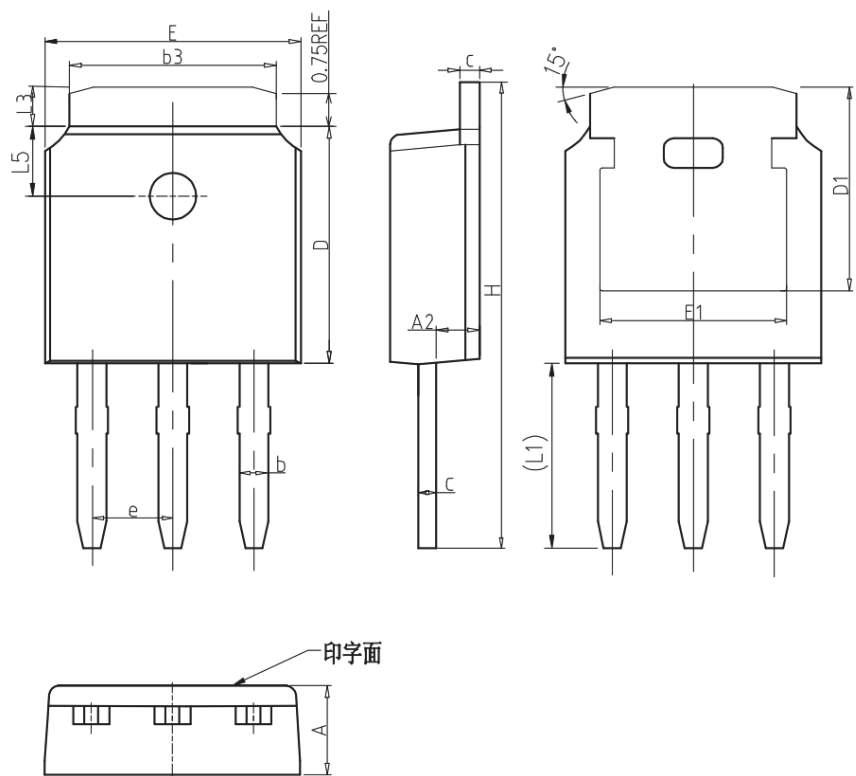


COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

HY3403D/U/V

TO-251-3S



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	10.00	11.22	11.44
L1	3.90	4.10	4.30
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168Hrs/500Hrs/1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -55°C~150°C

Customer Service

Worldwide Sales and Service: sales@hymexa.com

Technical Support: Technology@hymexa.com

Huayi Microelectronics Co., Ltd.

No.8928, Shangji Road, Economic and Technological Development Zone, Xi'an, China

TEL: (86-029) 86685706

FAX: (86-029) 86685705

E-mail: sales@hymexa.com

Web net: www.hymexa.com